

Post-Doctoral Position

Laboratoire d'accueil :
ICube,
département D-ESSP, équipe MaCÉPV
23 Rue du Loess, Strasbourg, France

Description of the job offer :

We are seeking candidates to work on development of **tandem InGaN/Silicon solar cells**.

The candidate selected will be in charge of the following actions:

- Fabrication of tunnel junctions between Si and InGaN
- Deposition of epi-ZnO buffer layer on Si
- Fabrication of the InGaN/Si cells and their photovoltaic characterisations

The candidate should have a solid background on materials science as well as on semiconductor physics and devices. He should have worked on Si and III-V materials. Strong knowledges on solar cells fabrications and characterizations are suited.

Duration: 24 months

Start: May , 2014

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